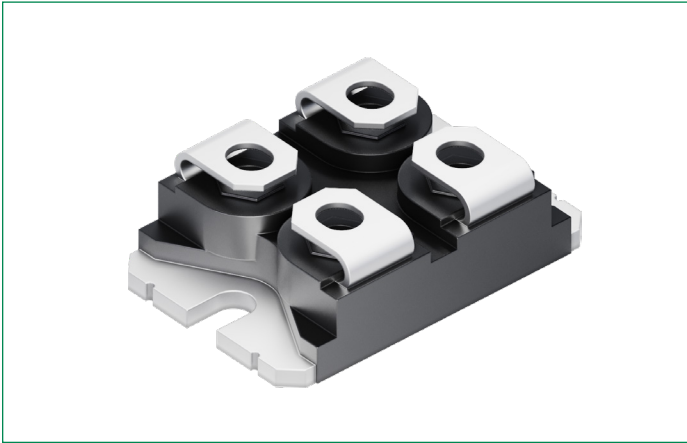


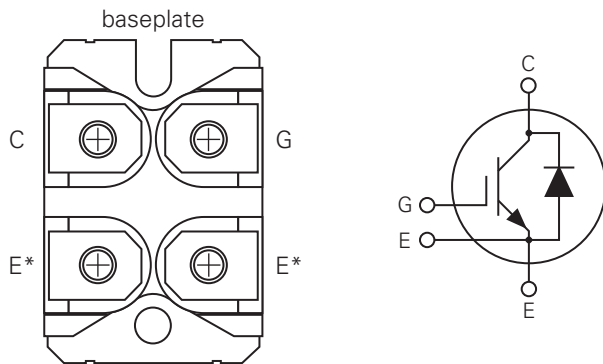
# IXYN110N120B4H1

## 1200 V, 110 A XPT™ Gen4 IGBT with Sonic Diode

Extreme Light Punch Through IGBT for 5–30 kHz Switching



### Pinout Diagram (SOT-227B)



**G:** Gate; **C:** Collector; **E:** Emitter; **baseplate:** Isolated  
 \*Either emitter terminal can be used as Main or Kelvin Emitter

### Description:

Developed using our proprietary XPT™ thin-wafer technology and state-of-the-art Trench IGBT process, these devices feature reduced thermal resistance, low energy losses, fast switching, low tail current, and high current densities.

### Features & Benefits:

- Optimized for 5–30kHz Switching
- miniBLOC, with Aluminium Nitride Isolation
- 2500V~ Isolation Voltage
- High Current Handling Capability
- Positive Thermal Coefficient of  $V_{CE(sat)}$
- High Power Density
- Low Gate Drive Requirement
- International Standard Package
- Anti-Parallel Sonic Diode

### Applications:

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines

### Product Summary

Characteristic	Value	Unit
$V_{CES}$	1200	V
$I_{C110}$	110	A
$V_{CE(sat)}$	2.10	V
$t_{fi(typ)}$	130	ns

## Maximum Ratings

Symbol	Characteristic	Conditions	Value	Unit
$V_{CES}$	Collector-Emitter Voltage	$T_{VJ} = 25\text{ °C to }175\text{ °C}$	1200	V
$V_{GES}$	Gate-Emitter Voltage	Continuous	$\pm 20$	V
$V_{GEM}$	Transient Gate-Emitter Voltage	Transient	$\pm 30$	V
$I_{C25}$	Continuous Collector Current	$T_C = 25\text{ °C}$	218	A
$I_{LRMS}$	Terminal Current Limit	–	200	A
$I_{C110}$	Continuous Collector Current	$T_C = 110\text{ °C}$	110	A
$I_{F110}$	Diode Forward Current	$T_C = 110\text{ °C}$	74	A
$I_{CM}$	Pulsed Collector Current	$T_C = 25\text{ °C}, 1\text{ ms}$	820	A
SSOA (RBSOA)	Switching Safe Operating Area (Reverse Biased Safe Operating Area)	$V_{GE} = 15\text{ V}, T_{VJ} = 150\text{ °C}, R_G = 2\ \Omega,$ $I_{CM} = 0.8 \times V_{CES}$	220	A
$P_C$	Collector Power Dissipation	$T_C = 25\text{ °C}$	830	W
$T_{VJ}$	Virtual Junction Temperature	–	–55 to 175	°C
$T_{stg}$	Storage Temperature	–	–55 to 175	°C
$V_{ISOL}$	Isolation Voltage	50/60 Hz, $I_{ISOL} \leq 1\text{ mA}, t = 1\text{ min}$	2500	V~
		50/60 Hz, $I_{ISOL} \leq 1\text{ mA}, t = 1\text{ s}$	3000	
$M_d$	Mounting Torque	–	1.5 / 13	Nm/lb.in
	Terminal Connection Torque	–	1.3 / 11.5	
W	Weight	–	30	g

## Thermal Characteristics

Symbol	Characteristic	Conditions	Value			Unit
			Min.	Typ.	Max.	
$R_{th, JC}$	Thermal Resistance, junction-to-case, IGBT	–	–	–	0.18	K/W
$R_{th, CS}$	Thermal Resistance, case-to-heat sink	–	–	0.05	–	K/W

## Electrical Characteristics – Static ( $T_{VJ} = 25\text{ °C}$ unless otherwise specified)

Symbol	Characteristic	Conditions	Value			Unit
			Min.	Typ.	Max.	
$BV_{CES}$	Collector-Emitter Breakdown Voltage	$I_C = 250\ \mu\text{A}, V_{GE} = 0\text{ V}$	1200	–	–	V
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C = 3\text{ mA}, V_{CE} = V_{GE}$	4.5	–	6.5	V
$I_{CES}$	Zero Gate Voltage Collector Current	$V_{CE} = V_{CES}, V_{GE} = 0\text{ V}$	–	–	50	$\mu\text{A}$
		$V_{CE} = V_{CES}, V_{GE} = 0\text{ V}, T_{VJ} = 125\text{ °C}$	–	–	7	mA
$I_{GES}$	Gate-Emitter Leakage Current	$V_{CE} = 0\text{ V}, V_{GE} = \pm 20\text{ V}$	–	–	$\pm 100$	nA
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage <sup>1</sup>	$I_C = I_{C110}, V_{GE} = 15\text{ V}$	–	1.66	2.10	V
		$I_C = I_{C110}, V_{GE} = 15\text{ V}, T_{VJ} = 150\text{ °C}$	–	1.95	–	V

**Note 1:** Pulse test,  $t \leq 300\ \mu\text{s}$ , duty cycle,  $d \leq 2\%$

**Electrical Characteristics – Dynamic** ( $T_{VJ} = 25\text{ °C}$  unless otherwise specified)

Symbol	Characteristic	Conditions	Value			Unit	
			Min.	Typ.	Max.		
$g_{fs}$	Transconductance <sup>1</sup>	$I_C = 55\text{ A}, V_{CE} = 10\text{ V}$	40	68	–	S	
$C_{ies}$	Input Capacitance	$V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$	–	5460	–	pF	
$C_{oes}$	Output Capacitance		–	480	–		
$C_{res}$	Reverse Transfer Capacitance		–	220	–		
$Q_{g(on)}$	Total Gate Charge	$I_C = I_{C110}, V_{GE} = 15\text{ V}, V_{CE} = 0.5 \times V_{CES}$	–	340	–	nC	
$Q_{ge}$	Gate-Emitter Charge		–	52	–		
$Q_{gc}$	Gate-Collector Charge		–	144	–		
$t_{d(on)}$	Turn-on Delay Time <sup>2</sup>	Inductive Load, $V_{GE} = 15\text{ V},$ $V_{CE} = 0.5 \times V_{CES},$ $I_C = 50\text{ A},$ $R_{G(ext)} = 2\ \Omega$	$T_{VJ} = 25\text{ °C}$	–	45	–	ns
			$T_{VJ} = 150\text{ °C}$	–	34	–	
$t_{ri}$	Turn-on Rise Time <sup>2</sup>		$T_{VJ} = 25\text{ °C}$	–	50	–	ns
			$T_{VJ} = 150\text{ °C}$	–	38	–	
$E_{on}$	Turn-on Energy <sup>2</sup>		$T_{VJ} = 25\text{ °C}$	–	3.60	–	mJ
			$T_{VJ} = 150\text{ °C}$	–	4.95	–	
$t_{d(off)}$	Turn-off Delay Time <sup>2</sup>		$T_{VJ} = 25\text{ °C}$	–	390	–	ns
			$T_{VJ} = 150\text{ °C}$	–	440	–	
$t_{fi}$	Turn-off Fall Time <sup>2</sup>		$T_{VJ} = 25\text{ °C}$	–	130	–	ns
			$T_{VJ} = 150\text{ °C}$	–	210	–	
$E_{off}$	Turn-off Energy <sup>2</sup>	$T_{VJ} = 25\text{ °C}$	–	3.85	–	mJ	
		$T_{VJ} = 150\text{ °C}$	–	6.45	–		

**Note 1:** Pulse test,  $t \leq 300\ \mu\text{s}$ , duty cycle,  $d \leq 2\%$

**Note 2:** Switching times and energy losses may increase for higher  $V_{CE(clamp)}$ ,  $T_{VJ}$ , or  $R_G$ .

**Reverse Sonic Diode (FRD)** ( $T_{VJ} = 25\text{ °C}$  unless otherwise specified)

Symbol	Characteristic	Conditions	Value			Unit
			Min.	Typ.	Max.	
$V_F$	Diode Forward Voltage <sup>1</sup>	$I_F = 100\text{ A}, V_{GE} = 0\text{ V}$	–	2.20	2.70	V
		$I_F = 100\text{ A}, V_{GE} = 0\text{ V}, T_{VJ} = 150\text{ °C}$	–	2.15	–	
$I_{RM}$	Reverse Recovery Current	$I_F = 50\text{ A}, V_{GE} = 0\text{ V}, T_{VJ} = 150\text{ °C}$	–	43	–	A
$t_{rr}$	Reverse Recovery Time	$-di_F/dt = 750\text{ A}/\mu\text{s}, V_R = 600\text{ V}$	–	270	–	ns
$R_{th, JC}$	Thermal Resistance, junction-to-case	–	–	–	0.41	K/W

**Note 1:** Pulse test,  $t \leq 300\ \mu\text{s}$ , duty cycle,  $d \leq 2\%$

Characteristic Curves

Fig. 1. Output Characteristics @  $T_{VJ} = 25\text{ }^{\circ}\text{C}$

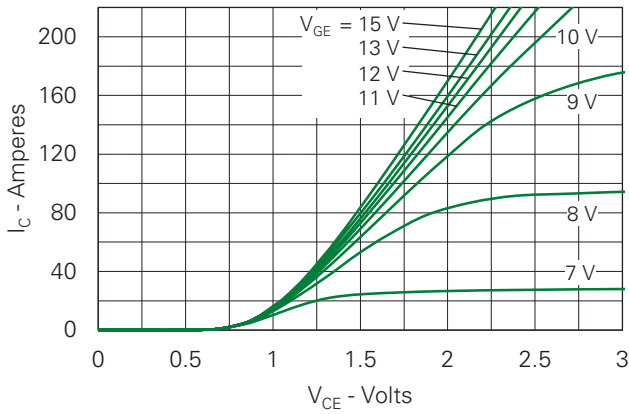


Fig. 2. Extended Output Characteristics @  $T_{VJ} = 25\text{ }^{\circ}\text{C}$

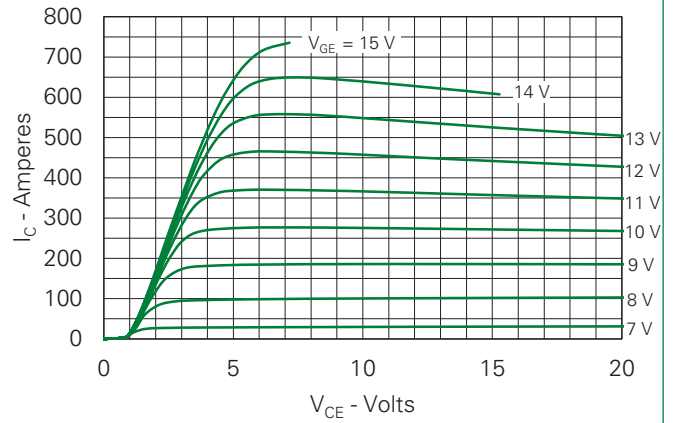


Fig. 3. Output Characteristics @  $T_{VJ} = 150\text{ }^{\circ}\text{C}$

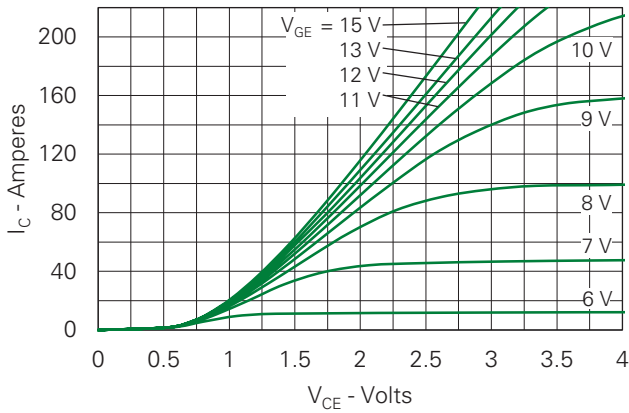


Fig. 4. Dependence of  $V_{CE(sat)}$  on Junction Temperature

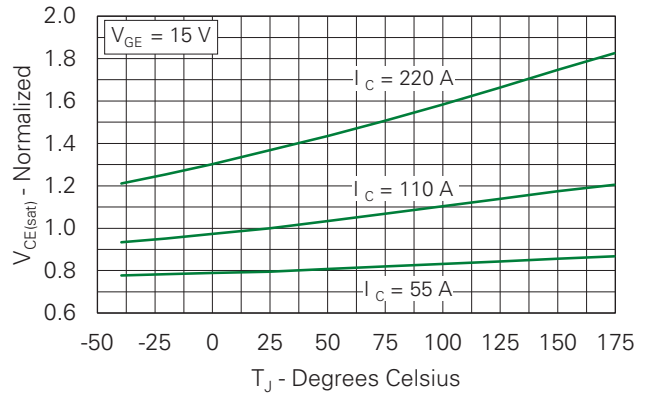


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

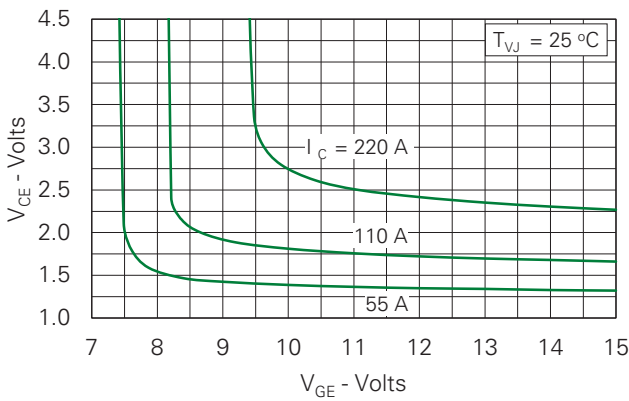
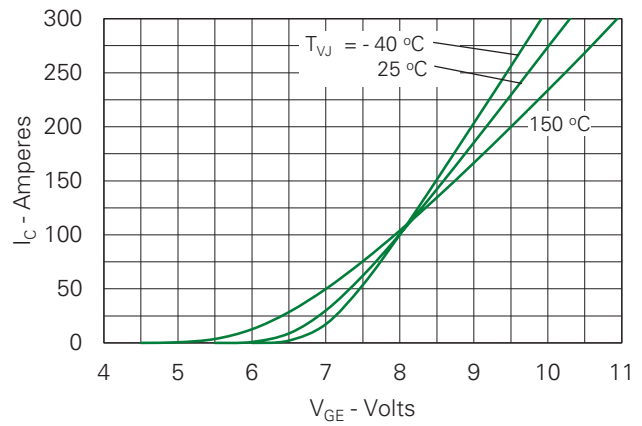
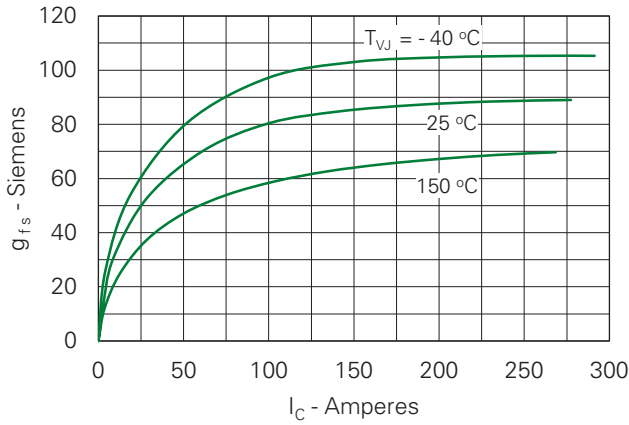


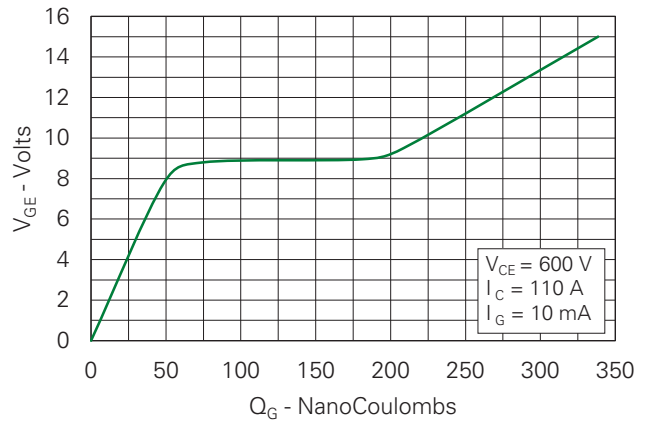
Fig. 6. Input Admittance



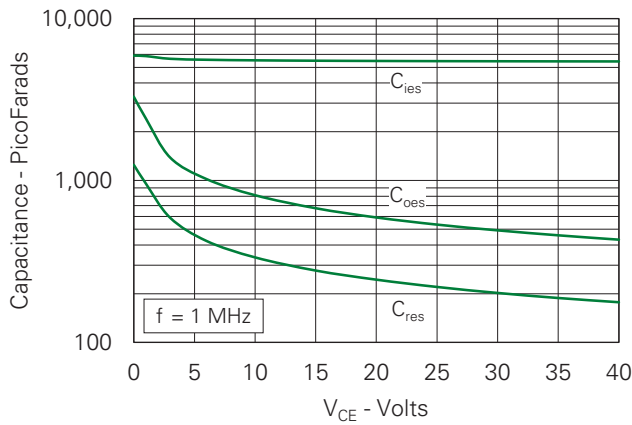
**Fig. 7. Transconductance**



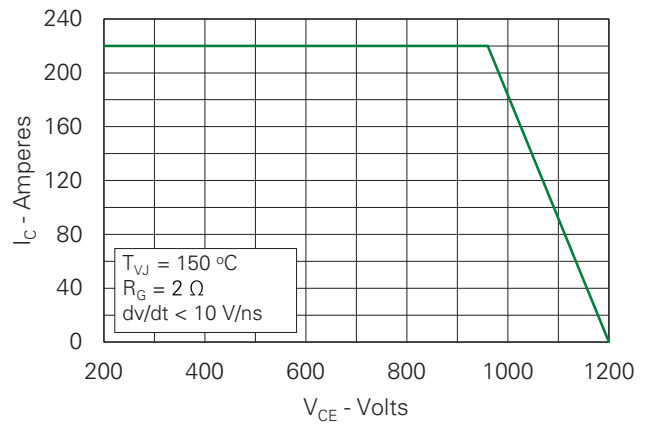
**Fig. 8. Gate Charge**



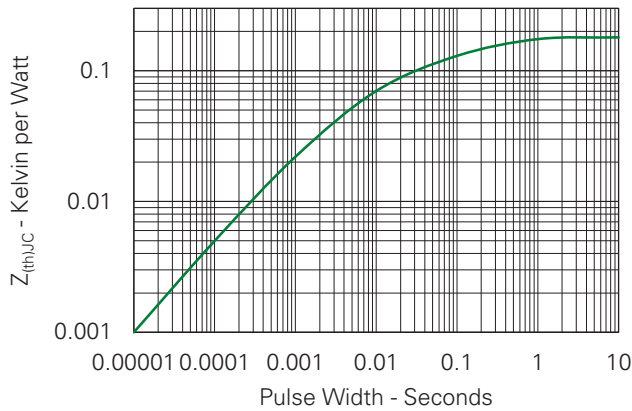
**Fig. 9. Capacitance**



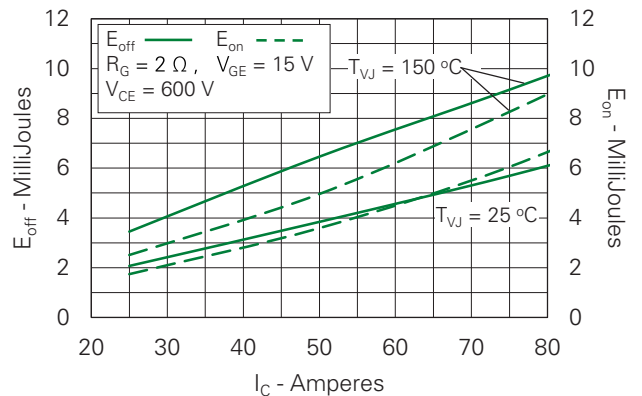
**Fig. 10. Reverse-Bias Safe Operating Area**



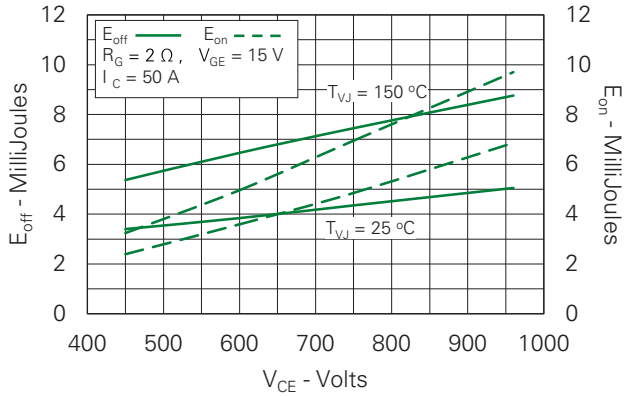
**Fig. 11. Maximum Transient Thermal Impedance**



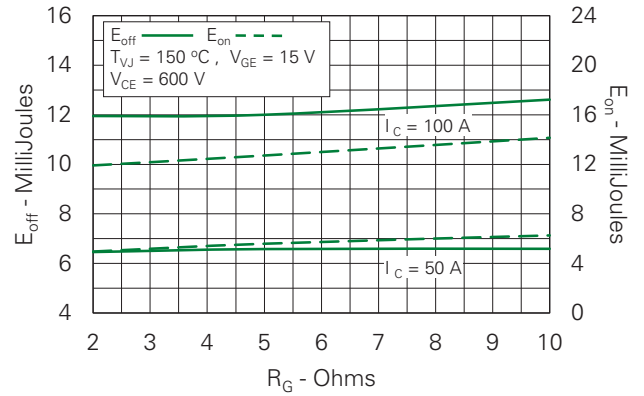
**Fig. 12. Inductive Switching Energy Loss vs. Collector Current**



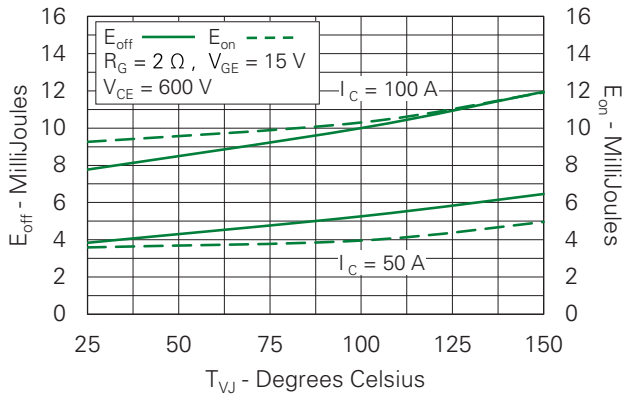
**Fig. 13. Inductive Switching Energy Loss vs. Collector-Emitter Voltage**



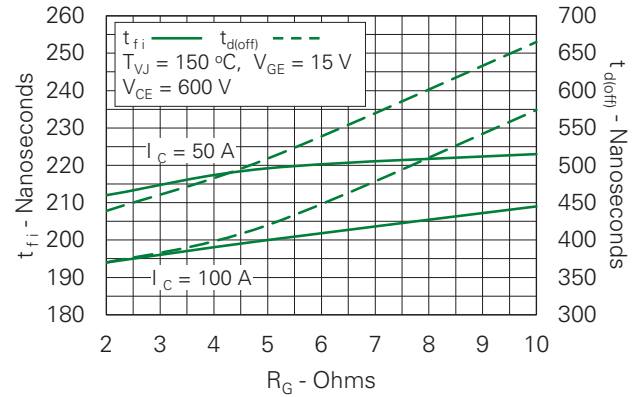
**Fig. 14. Inductive Switching Energy Loss vs. Gate Resistance**



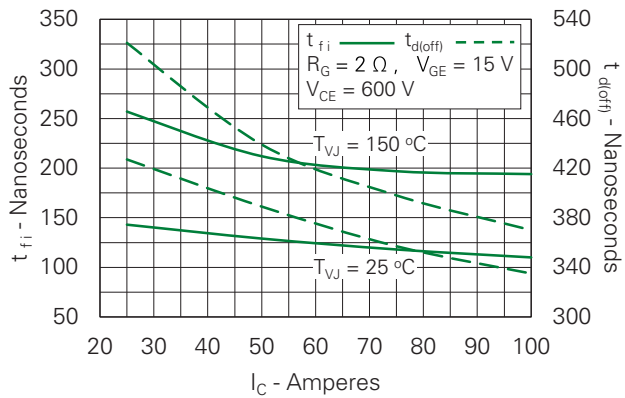
**Fig. 15. Inductive Switching Energy Loss vs. Junction Temperature**



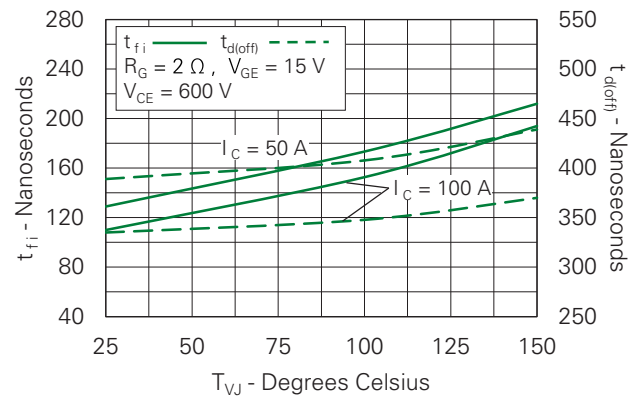
**Fig. 16. Inductive Turn-off Switching Times vs. Gate Resistance**



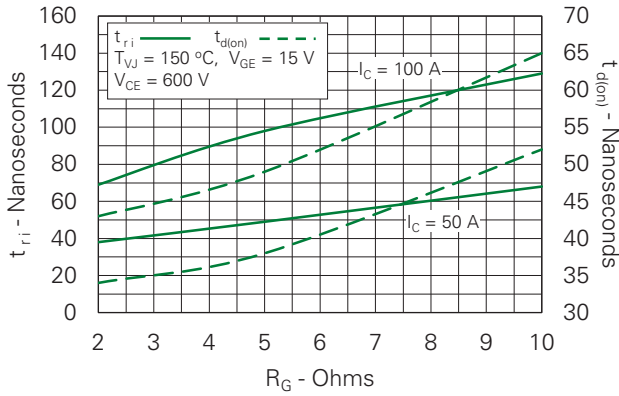
**Fig. 17. Inductive Turn-off Switching Times vs. Collector Current**



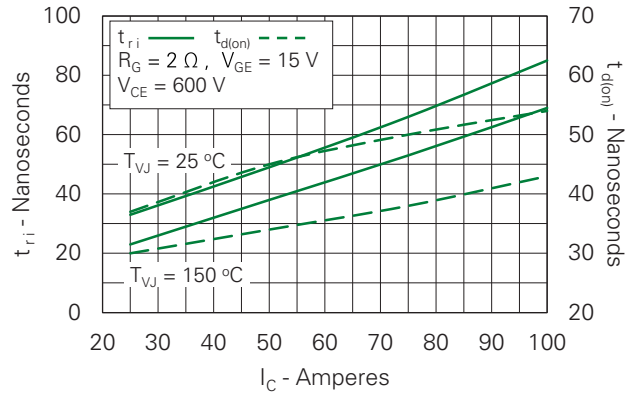
**Fig. 18. Inductive Turn-off Switching Times vs. Junction Temperature**



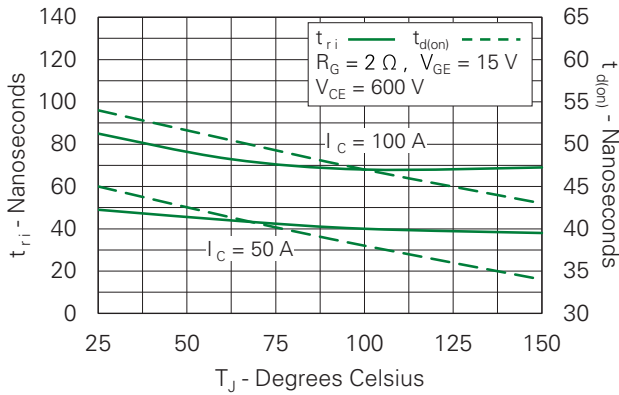
**Fig. 19. Inductive Turn-on Switching Times vs. Gate Resistance**



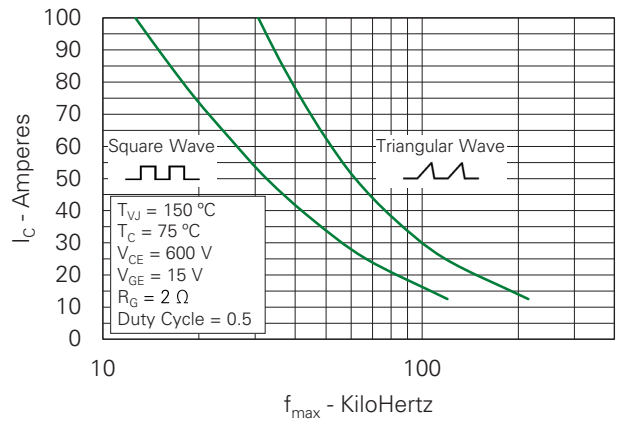
**Fig. 20. Inductive Turn-on Switching Times vs. Collector Current**



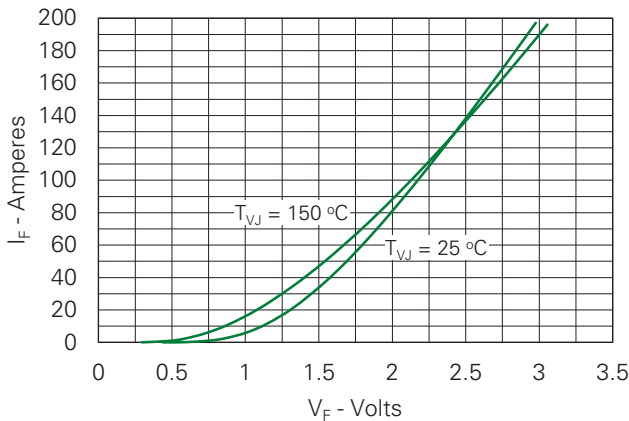
**Fig. 21. Inductive Turn-on Switching Times vs. Junction Temperature**



**Fig. 22. Maximum Peak Load Current vs. Frequency**



**Fig. 23. Diode Forward Characteristics**



**Fig. 24. Reverse Recovery Charge vs. -di\_F/dt**

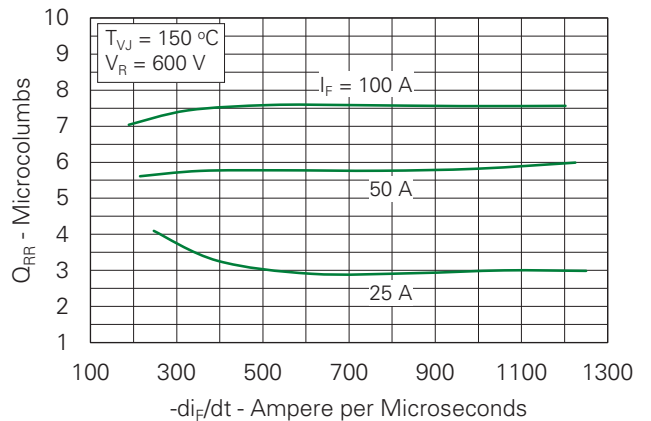


Fig. 25 Reverse Recovery Current vs.  $-di_F/dt$

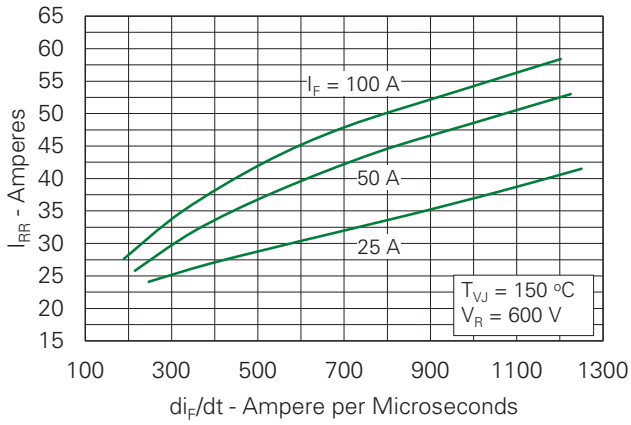


Fig. 26. Reverse Recovery Time vs.  $-di_F/dt$

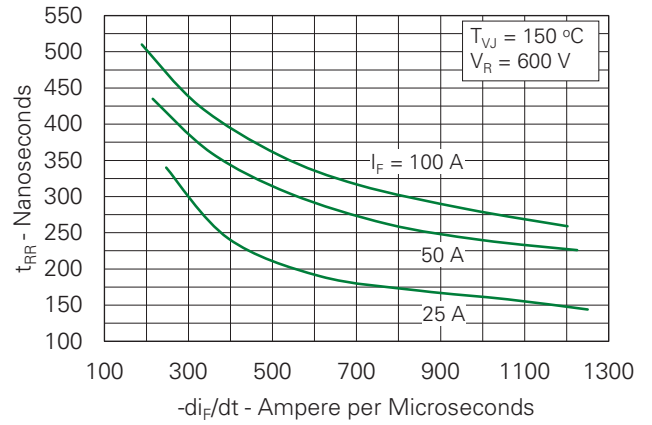


Fig. 27. Dynamic Parameters  $Q_{RR}$ ,  $I_{RR}$  vs. Junction Temperature

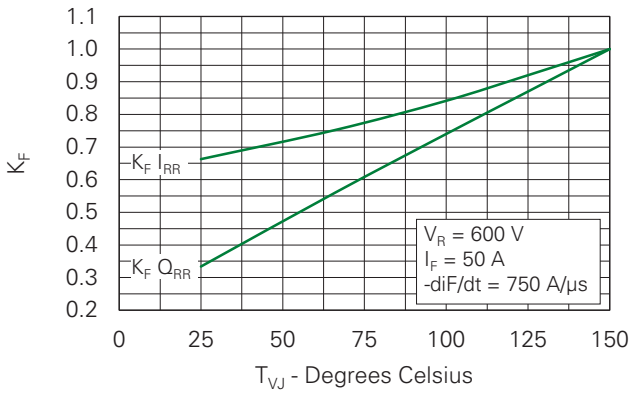
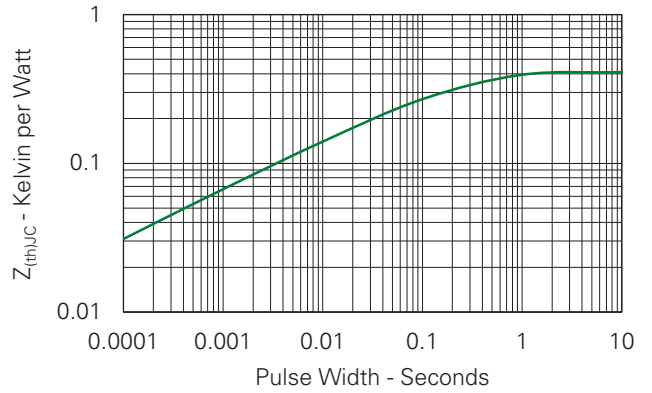
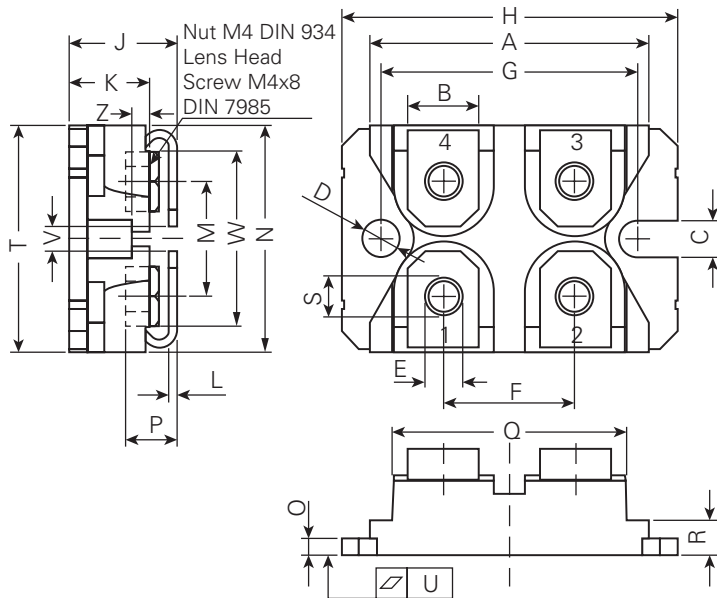


Fig. 28. Maximum Transient Thermal Impedance (Diode)





## Part Outline Drawing (SOT-227B)



Symbol	Inches			Millimeters		
	Min.	Typical	Max.	Min.	Typical	Max
A	1.240	-	1.255	31.50	-	31.88
B	0.307	-	0.323	7.80	-	8.20
C	0.161	-	0.169	4.09	-	4.29
D	0.161	-	0.169	4.09	-	4.29
E	0.161	-	0.169	4.09	-	4.29
F	0.587	-	0.595	14.91	-	15.11
G	1.186	-	1.193	30.12	-	30.30
H	1.488	-	1.505	37.80	-	38.23
J	0.460	-	0.481	11.68	-	12.22
K	0.351	-	0.378	8.92	-	9.60
L	0.029	-	0.033	0.74	-	0.84
M	0.492	-	0.516	12.50	-	13.10
N	0.990	-	1.001	25.15	-	25.42
O	0.077	-	0.084	1.95	-	2.13
P	0.195	-	0.244	4.95	-	6.20
Q	1.045	-	1.059	26.54	-	26.90
R	0.155	-	0.174	3.94	-	4.42
S	0.179	-	0.191	4.55	-	4.85
T	0.968	-	0.994	24.59	-	25.25
U	-0.002	-	0.004	-0.05	-	0.10
V	0.126	-	0.217	3.20	-	5.50
W	0.780	-	0.830	19.81	-	21.08
Z	0.098	-	0.106	2.50	-	2.70

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